2SA0879 (2SA879)

Silicon PNP epitaxial planar type

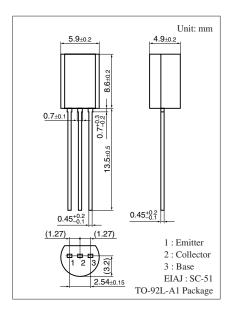
For general amplification Complementary to 2SC1573

■ Features

 \bullet High collector-emitter voltage (Base open) V_{CEO}

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V _{CBO}	-250	V
Collector-emitter voltage (Base open)	V _{CEO}	-200	V
Emitter-base voltage (Collector open)	V_{EBO}	-5	V
Collector current	I_{C}	-70	mA
Peak collector current	I_{CP}	-100	mA
Collector power dissipation	P _C	1	W
Junction temperature	T_{j}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C



■ Electrical Characteristics $T_a = 25$ °C ± 3 °C

Symbol	Conditions	Min	Тур	Max	Unit
V _{CEO}	$I_C = -100 \ \mu A, I_B = 0$	-200			V
V _{EBO}	$I_E = -1 \mu A, I_C = 0$	-5			V
h _{FE}	$V_{CE} = -10 \text{ V}, \ I_{C} = -5 \text{ mA}$	60		220	_
V _{CE(sat)}	$I_C = -50 \text{ mA}, I_B = -5 \text{ mA}$			-1.5	V
f_T	$V_{CB} = -10 \text{ V}, I_E = 10 \text{ mA}, f = 200 \text{ MHz}$	50	80		MHz
C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		5	10	pF
	V_{CEO} V_{EBO} h_{FE} $V_{CE(sat)}$ f_{T}	$\begin{split} &V_{CEO} &I_{C} = -100 \ \mu\text{A}, \ I_{B} = 0 \\ &V_{EBO} &I_{E} = -1 \ \mu\text{A}, \ I_{C} = 0 \\ &h_{FE} &V_{CE} = -10 \ V, \ I_{C} = -5 \ m\text{A} \\ &V_{CE(sat)} &I_{C} = -50 \ m\text{A}, \ I_{B} = -5 \ m\text{A} \\ &f_{T} &V_{CB} = -10 \ V, \ I_{E} = 10 \ m\text{A}, \ f = 200 \ \text{MHz} \end{split}$	$\begin{array}{ccccc} V_{CEO} & I_{C} = -100 \ \mu\text{A}, \ I_{B} = 0 & -200 \\ \\ V_{EBO} & I_{E} = -1 \ \mu\text{A}, \ I_{C} = 0 & -5 \\ \\ h_{FE} & V_{CE} = -10 \ V, \ I_{C} = -5 \ \text{mA} & 60 \\ \\ V_{CE(sat)} & I_{C} = -50 \ \text{mA}, \ I_{B} = -5 \ \text{mA} \\ \\ f_{T} & V_{CB} = -10 \ V, \ I_{E} = 10 \ \text{mA}, \ f = 200 \ \text{MHz} & 50 \\ \\ \end{array}$	$\begin{array}{cccccccccccccccccccccccccccccccccccc$	$\begin{array}{cccccccccccccccccccccccccccccccccccc$

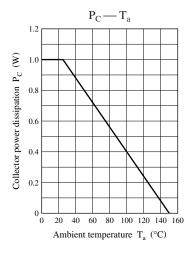
 $Note) \ 1. \ Measuring \ methods \ are \ based \ on \ JAPANESE \ INDUSTRIAL \ STANDARD \ JIS \ C \ 7030 \ measuring \ methods \ for \ transistors.$

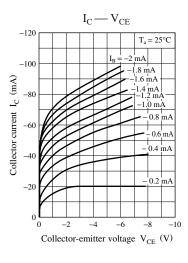
2. *: Rank classification

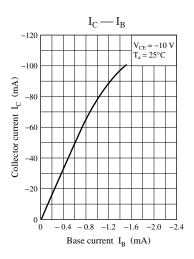
Rank	Q	R
h_{FE}	60 to 150	100 to 220

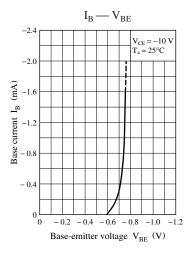
Note) The part number in the parenthesis shows conventional part number.

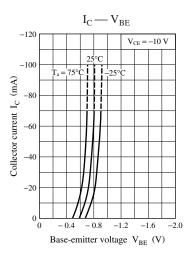
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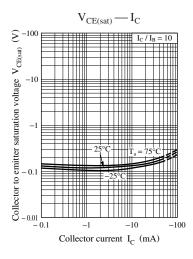


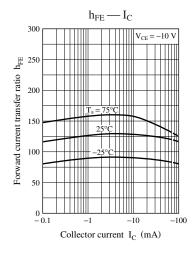


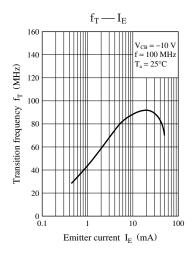


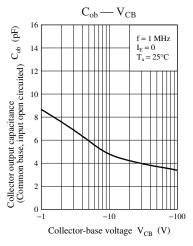


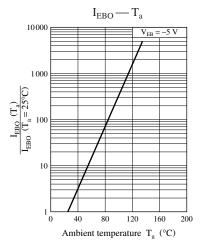


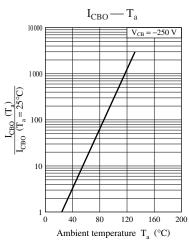


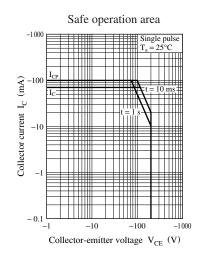












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